Boca Semiconductor Corp. (BSC)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	150	Vdc
Collector-Base Voltage	VCBO	150	Vdc
Emitter-Base Voltage	VEBO	6.0	Vdc
Collector Current — Continuous	lc	300	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	1.0 5.71	Watt mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R _{0JA}	175	°C/W
Thermal Resistance, Junction to Case	ReJC	35	°C/W

2N3500 2N3501*

CASE 79-04, STYLE 1 TO-39 (TO-205AD)





GENERAL PURPOSE TRANSISTORS

NPN SILICON

★2N3501 is a Motorola designated preferred device.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (1) (I _C = 10 mAdc, I _B = 0)	2N3500, 2N3501	V(BR)CEO	150	_	_	Vdc
Collector-Base Breakdown Voltage $(I_C = 10 \mu Adc, I_E = 0)$	2N3500, 2N3501	V _(BR) CBO	150	_	_	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μ Adc, I _C = 0)		V _{(BR)EBO}	6.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 75 Vdc, I _E = 0) (V _{CB} = 75 Vdc, I _E = 0, T _A = 150°C)	2N3500, 2N3501	СВО		_	0.05 50	μAdc
Emitter Cutoff Current (VEB(off) = 4 0 Vdc, I _C = 0)		¹ EBO	_	_	25	nAdc
ON CHARACTERISTICS	·					
DC Current Gain ($I_C = 0.1 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) (1)	2N3500 2N3501 2N3500 2N3501 2N3500	hFE	20 35 25 50 35 75	_ _ _ _	_ _ _ _	_
(I _C = 150 mAdc, V_{CE} = 10 Vdc) (1) (I _C = 300 mAdc, V_{CE} = 10 Vdc) (1)	2N3501 2N3500 2N3501 2N3500 2N3501		40 100 15 20	_ 	120 300 — —	
Collector-Emitter Saturation Voltage (1) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5 0 mAdc) (I _C = 150 mAdc, I _B = 15 mAdc)	All Types All Types 2N3500, 2N3501	VCE(sat)		=	0.2 0 25 0.4	Vdc

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^{\circ}C$ unless otherwise noted.)

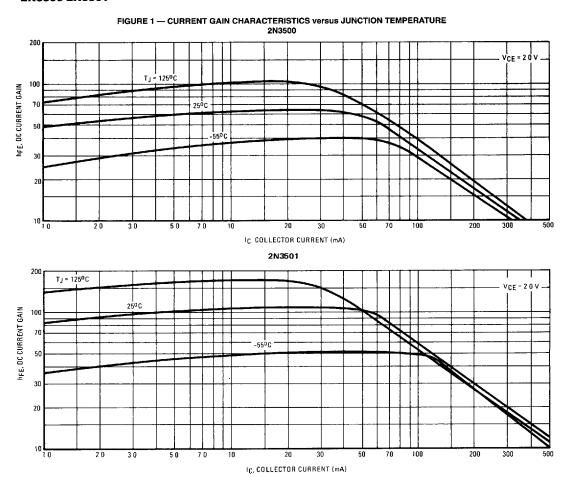
Characteristic		Symbol	Min	Тур	Max	Unit
Base-Emitter Saturation Voltage (1) (IC = 10 mAdc, IB = 1.0 mAdc) (IC = 50 mAdc, IB = 5.0 mAdc) (IC = 150 mAdc, IB = 15 mAdc)	All Types All Types 2N3500, 2N3501	VBE(sat)	=	_ _ _	0.8 0 9 1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (2) (V _{CE} = 20 Vdc, I _C = 20 mAdc, f = 100 MHz)		fŢ	150	_	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 0 MHz)	2N3500, 2N3501	copo		_	8.0	pF
Input Capacitance (VEB = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	_	80	pF
Input Impedance (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3500 2N3501	h _{le}	0.2 0.25	_	1.0 1.25	k ohms
Voltage Feedback Ratio (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3500 2N3501	h _{re}	_	=	2.5 4.0	X 10 ⁻⁴
Small-Signal Current Gain (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3500 2N3501	h _{fe}	50 75	_	300 375	_
Output Admittance (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1 0 kHz)	2N3500 2N3501	h _{oe}	_	=	100 200	μmhos
SWITCHING CHARACTERISTICS				,	•	
Delay Time (I _C = 150 mAdc, I _{B1} = 15 mAdc, V _{CC} = 100 Vdc	V _{BE(off)} = -2.0 Vdc)	t _d	_	20		ns
Rise Time (I _C = 150 mAdc, I _{B1} = 15 mAdc, V _{CC} = 100 Vdc, V _{BE(off)} = -2.0 Vdc)		t _r	_	35	_	ns
Storage Time ($I_C = 150 \text{ mAdc}$, $I_{B1} = I_{B2} = 15 \text{ mAdc}$, $V_{CC} = 100 \text{ Vdc}$)		t _S	_	800	_	ns
Fall Time (I _C = 150 mAdc, I _{B1} = I _{B2} = 15 mAdc, V _{CC} = 100 Vdc)		t _f	_	80		ns

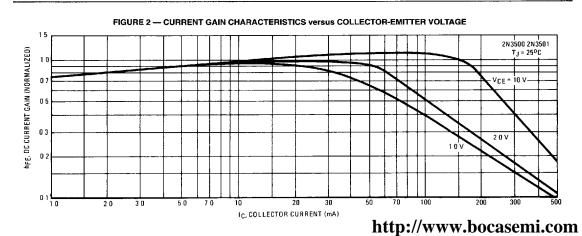
⁽¹⁾ Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2 0%

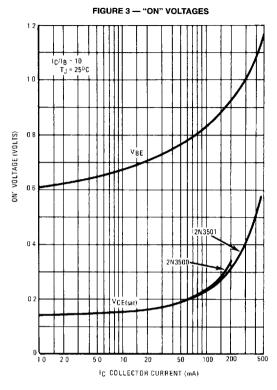
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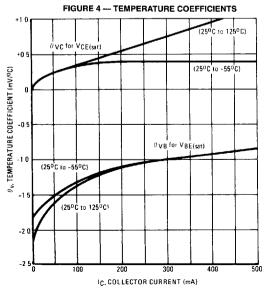
⁽²⁾ f_T = lh_{fe}l • f_{test}.

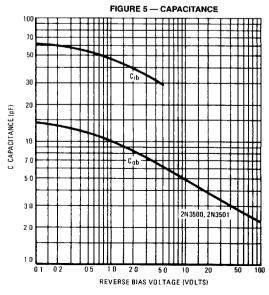
2N3500 2N3501











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AUDIO SMALL-SIGNAL h PARAMETER CHARACTERISTICS

(VCE = 10 Vdc, TA = 25°C, f = 1.0 kHz)

